

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A method for manufacturing a thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;

forming a base film over the peel-off layer;

forming a plurality of thin film integrated circuit devices over the base film;

forming a groove at a boundary between the plurality of thin film integrated circuit devices; and

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices,

wherein the substrate is a glass substrate or a quartz substrate.

2. (Previously Presented) A method for manufacturing a thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;

forming a base film over the peel-off layer;

forming a plurality of thin film integrated circuit devices over the base film;

forming a groove at a boundary between the plurality of thin film integrated circuit devices;

attaching a jig to an upper portion of the plurality of thin film integrated circuit devices;

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices; and

removing the jig attached to the plurality of thin film integrated circuit devices, wherein the substrate is a glass substrate or a quartz substrate.

3. (Previously Presented) A method for manufacturing a thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;

forming a base film over the peel-off layer;

forming a plurality of thin film integrated circuits over the base film;

forming an insulating film over the plurality of thin film integrated circuits, thereby forming a plurality of thin film integrated circuit devices;

forming a groove at a boundary between the plurality of thin film integrated circuit devices; and

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices,

wherein the substrate is a glass substrate or a quartz substrate.

4. (Previously Presented) A method for manufacturing a thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;

forming a base film over the peel-off layer;

forming a plurality of thin film integrated circuits over the base film;

forming an insulating film over the plurality of thin film integrated circuits, thereby forming a plurality of thin film integrated circuit devices;

forming a groove at a boundary between the plurality of thin film integrated circuit devices;

attaching a jig to an upper portion of the plurality of thin film integrated circuit devices;

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices; and

removing the jig attached to the plurality of thin film integrated circuit devices, wherein the substrate is a glass substrate or a quartz substrate.

5. (Original) A method for manufacturing a thin film integrated circuit device according to Claim 2 or Claim 4, wherein the jig is attached using an adhesive material whose adhesive force is reduced or lost by UV light irradiation.

6. (Previously Presented) A method for manufacturing a thin film integrated circuit device according to Claim 3 or Claim 4, wherein the insulating film contains a material that has a skeletal structure including a bond of silicon and oxygen and includes at least hydrogen as a substituent or at least one selected from the group consisting of fluorine, an alkyl group, and an aromatic hydrocarbon as the substituent.

7. (Original) A method for manufacturing a thin film integrated circuit device according to any one of Claims 1 through 4, wherein the peel-off layer contains silicon as a main component.

8. (Original) A method for manufacturing a thin film integrated circuit device according to any one of Claims 1 through 4, wherein the base film contains one selected from silicon oxide, silicon nitride, and silicon oxide containing nitrogen.

9. (Original) A method for manufacturing a thin film integrated circuit device according to any one of Claims 1 through 4, wherein the groove is formed by dicing or dry etching.

10. (Canceled)

11. (Original) A method for manufacturing a thin film integrated circuit device according to any one of Claims 1 through 4, wherein the halogen fluoride is ClF_3 (chlorine trifluoride).

12. (Previously Presented) A method for manufacturing a noncontact thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;

forming a base film over the peel-off layer;

forming a plurality of thin film integrated circuits over the base film;

forming an insulating film over the plurality of thin film integrated circuits, thereby forming a plurality of thin film integrated circuit devices;

forming a groove at a boundary between the plurality of thin film integrated circuit devices;

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices; and

forming an antenna on an upper or lower portion of the plurality of thin film integrated circuit devices,

wherein the substrate is a glass substrate or a quartz substrate.

13. (Previously Presented) A method for manufacturing a noncontact thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a substrate;
forming a base film over the peel-off layer;
forming a plurality of thin film integrated circuits over the base film;
forming an insulating film over the plurality of thin film integrated circuits, thereby forming a plurality of thin film integrated circuit devices;
forming a groove at a boundary between the plurality of thin film integrated circuit devices;
attaching a jig to an upper portion of the plurality of thin film integrated circuit devices;
introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices;
removing the jig attached to the plurality of thin film integrated circuit devices;
and
forming an antenna on an upper or lower portion of the plurality of thin film integrated circuit devices,
wherein the substrate is a glass substrate or a quartz substrate.

14. (Currently Amended) A method for manufacturing a noncontact thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a first substrate;
forming a base film over the peel-off layer;
forming a plurality of thin film integrated circuit devices over the base film;
forming a groove at a boundary between the plurality of thin film integrated circuit devices;
introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices; and

enfolding at least one of the thin film integrated circuit devices with a substrate provided with an antenna,
wherein the first substrate is a glass substrate or a quartz substrate.

15. (Previously Presented) A method for manufacturing a noncontact thin film integrated circuit device comprising the steps of:

forming a peel-off layer over a first substrate;
forming a base film over the peel-off layer;
forming a plurality of thin film integrated circuit devices over the base film;
forming a groove at a boundary between the plurality of thin film integrated circuit devices;

attaching a jig to an upper portion of the plurality of thin film integrated circuit devices;

introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer, thereby separating the plurality of thin film integrated circuit devices;

removing the jig attached to the plurality of thin film integrated circuit devices;
and

enfolding at least one of the thin film integrated circuit devices with a substrate provided with an antenna,
wherein the first substrate is a glass substrate or a quartz substrate.

16. (Previously Presented) A method for manufacturing a noncontact thin film integrated circuit device according to Claim 13 or Claim 15, wherein the jig is attached using an adhesive material whose adhesive force is reduced or lost by UV light irradiation.

17. (Previously Presented) A method for manufacturing a noncontact thin film integrated circuit device according to Claim 12 or Claim 13, wherein the insulating film contains a material that has a skeletal structure including a bond of silicon and oxygen and includes at least hydrogen as a substituent or at least one selected from the group consisting of fluorine, an alkyl group, and an aromatic hydrocarbon as the substituent.

18. (Original) A method for manufacturing a noncontact thin film integrated circuit device according to any one of Claims 12 through 15, wherein the peel-off layer contains silicon as a main component.

19. (Original) A method for manufacturing a noncontact thin film integrated circuit device according to any one of Claims 12 through 15, wherein the base film contains one selected from silicon oxide, silicon nitride, and silicon oxide containing nitrogen.

20. (Original) A method for manufacturing a noncontact thin film integrated circuit device according to any one of Claims 12 through 15, wherein the groove is formed by dicing or dry etching.

21. (Canceled)

22. (Original) A method for manufacturing a noncontact thin film integrated circuit device according to any one of Claims 12 through 15, wherein the halogen fluoride is ClF_3 (chlorine trifluoride).

23.-30. (Canceled)